

2SD2423

Silicon NPN Epitaxial

Application

Low frequency power amplifier

Features

- The transistor with a built-in zener diode of surge absorb.

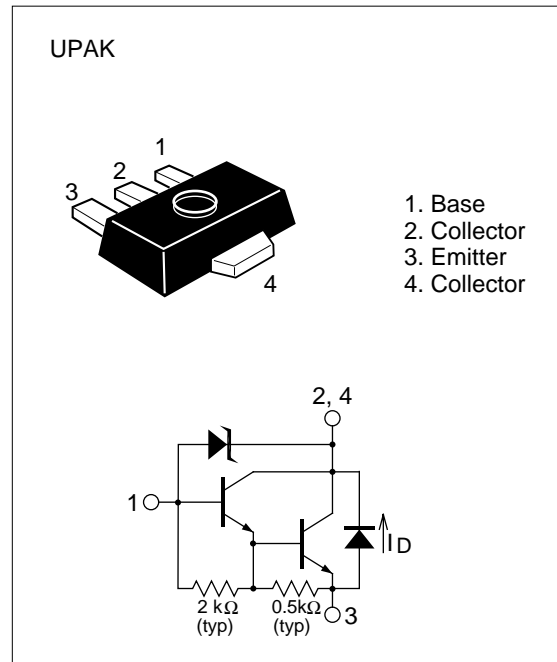


Table 1 Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	50	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_{C}	1.5	A
Collector power dissipation	P_{C}^*	1	W
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Collector to emitter diode forward current	I_{D}	1.5	A

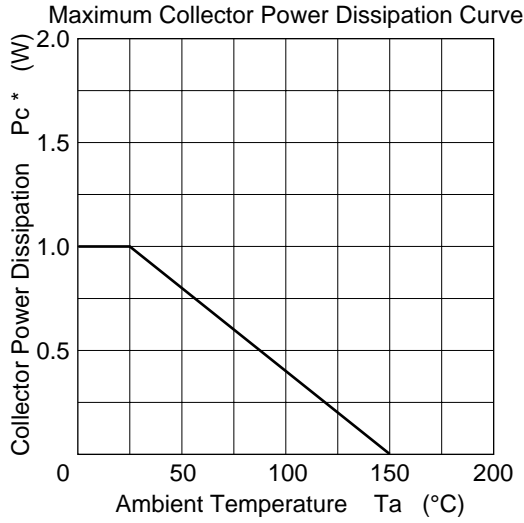
Note: * When using the ceramic board 0.7 mm thick (12.5 mm x 20 mm).

2SD2423

Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	50	—	70	V	$I_C = 100 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 10 \text{ mA}, R_{BE} = \infty$
Collector to emitter sustain voltage	$V_{CEO(sus)}$	50	—	70	V	$I_C = 1.5 \text{ A}, R_{BE} = \infty$ $L = 10 \text{ mH}^*$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 50 \text{ mA}, I_C = 0$
Collector cutoff current	I_{CEO}	—	—	10	μA	$V_{CE} = 40 \text{ V}, R_{BE} = \infty$
DC current transfer ratio	h_{FE}	2000	—	10000		$V_{CE} = 3 \text{ V}, I_C = 1 \text{ A}^*$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	1.5	V	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}^*$
Collector to emitter saturation voltage	$V_{CE(sat)2}$	—	—	2.3	V	$I_C = 1.5 \text{ A},$ $I_B = 1.5 \text{ mA}^*$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	2.0	V	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}^*$
Base to emitter saturation voltage	$V_{BE(sat)2}$	—	—	2.5	V	$I_C = 1.5 \text{ A},$ $I_B = 1.5 \text{ mA}^*$
Collector to emitter diode forward voltage	V_D	—	—	3.5	V	$I_D = 1.5 \text{ A}^*$

Note: Pulse test



* When using the ceramic board 0.7 mm thick.
(12.5 mm x 20 mm)

